



Stud Diode

Rectifier Diode

SKN 262

Features

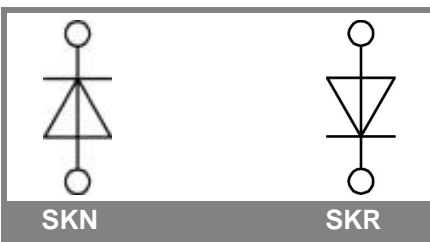
- Reverse voltages up to 2800 V
- Hermetic metal case with ceramic insulator with extra long creepage distances
- Threaded stud ISO M16 x 1,5
- Also available with threaded stud 3/4"-16 UNF 2A (e.g. SKN 262/24 UNF)
- SKN: anode to stud
- SKR: cathode to stud

Typical Applications

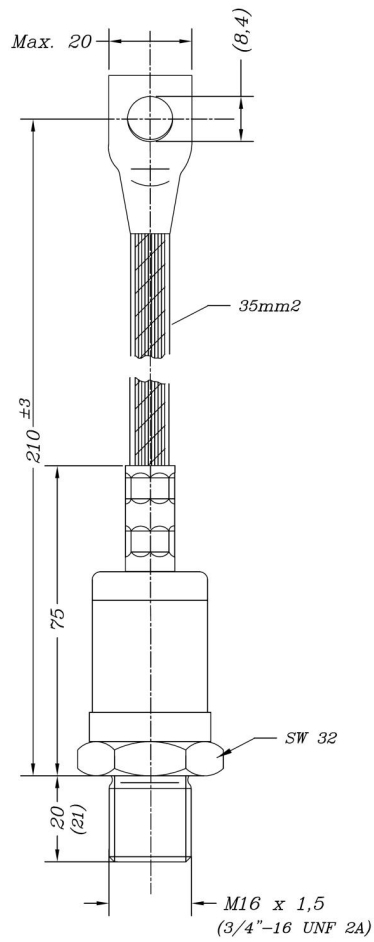
- High voltage rectifier diode, especially for traction applications
- Cooling via heatsinks
- Non-controllable and half-controllable rectifiers
- Free-wheeling diodes
- Recommended snubber network:
RC: 1 μ F, 20 Ω ($P_R = 2$ W),
 $R_p = 25$ k Ω ($P_R = 20$ W)

V_{RSM} V	V_{RRM} V	$I_{FRMS} = 500$ A (maximum value for continuous operation) $I_{FAV} = 260$ A (sin. 180; $T_c = 119$ °C)		
2000	2000	SKN 262/20	SKR 262/20	
2200	2200	SKN 262/22	SKR 262/22	
2400	2400	SKN 262/24	SKR 262/24	
2600	2600	SKN 262/26	SKR 262/26	
2800	2800	SKN 262/28	SKR 262/28	

Symbol	Conditions	Values	Units
I_{FAV}	sin. 180; $T_c = 100$ (125) °C	320 (240)	A
I_D	K 0,55; $T_a = 45$ °C; B2 / B6	335 / 480	A
	K 0,55F; $T_a = 35$ °C; B2 / B6	600 / 860	A
I_{FSM}	$T_{vj} = 25$ °C; 10 ms	6000	A
	$T_{vj} = 180$ °C; 10 ms	5000	A
i^2t	$T_{vj} = 25$ °C; 8,3 ... 10 ms	180000	A ² s
	$T_{vj} = 180$ °C; 8,3 ... 10 ms	125000	A ² s
V_F	$T_{vj} = 25$ °C; $I_F = 750$ A	max. 1,4	V
$V_{(TO)}$	$T_{vj} = 180$ °C	max. 0,85	V
r_T	$T_{vj} = 180$ °C	max. 0,6	m Ω
I_{RD}	$T_{vj} = 180$ °C; $V_{RD} = V_{RRM}$	max. 60	mA
Q_{rr}	$T_{vj} = 160$ °C; $-di_F/dt = 10$ A/ μ s	200	μ C
$R_{th(j-c)}$		0,2	K/W
$R_{th(c-s)}$		0,03	K/W
T_{vj}		- 40 ... + 180	°C
T_{stg}		- 55 ... + 180	°C
V_{isol}		-	V~
M_s	to heatsink (SI units)	30	Nm
M_s	to heatsink (US units)	270	lb.in.
a		5 * 9,81	m/s ²
m	approx.	260	g
Case			



Dimensions in mm



Case

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